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METHODS OF FORMING INTEGRATED CIRCUITS USING MASKS TO
PROVIDE ION IMPLANTATION SHIELDING TO PORTIONS OF A
SUBSTRATE ADJACENT TO AN ISOLATION REGION THEREIN AND
INTEGRATED CIRCUITS FORMED USING SAME

ABSTRACT

Methods of forming a channel region between isolation regions of an integrated circuit substrate are disclosed. In particular, a mask can be formed on an isolation region that extends onto a portion of the substrate adjacent to the isolation region to provide a shielded portion of the substrate adjacent to the isolation region and an exposed portion of the substrate spaced apart from the isolation region having the shielded portion therebetween. A channel region can be formed in the exposed portion of the substrate. Related integrated circuits are also discussed.